

PNP SILICON DARLINGTONS POWER TRANSISTORS

They are silicon epitaxial base transistors mounted in TO-3PN. They are designed for audio output stages and general amplifier and switching applications. complementary is BDV67-A-B-C Compliance to RoHS.

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings		Value	Unit	
		BDV66	-80		
.,	Callantan Emittan Valtana	BDV66A	-100		
V _{CEO}	Collector-Emitter Voltage	BDV66B	-120	V	
		BDV66C	-140		
		BDV66	-80	V	
.,	Callagtan Daga Valtaga	BDV66A	-100		
V _{CBO}	Collector-Base Voltage	BDV66B	-120		
		BDV66C	-140		
		BDV66		V	
\ /	Emitter-Base Voltage	BDV66A	-5.0		
V _{EBO}		BDV66B			
		BDV66C			
		BDV66		A	
I _C	Collector Current	BDV66A	-16		
ıC		BDV66B			
		BDV66C			
	Collector Peak Current	BDV66			
I _{CM}		BDV66A	-20		
	Concetor r can ourient	BDV66B	-20		
		BDV66C			
l _B		BDV66			
	Base Current	BDV66A	-0.5	А	
	Dasc Ourion	BDV66B	-0.5		
		BDV66C			



ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings			Value	Unit
			BDV66		
В	Power Dissipation	BDV66A	175	Watts	
P _T		$T_{mb} = 25^{\circ} C$	BDV66B	- 1/5	vvalls
			BDV66C		
	Junction Temperature		BDV66		°C
-			BDV66A	150	
TJ			BDV66B	130	
		BDV66C			
			BDV66		C
_	Storage Temperature		BDV66A	-65 to +150	
Ts	Storage remperature		BDV66B	-05 10 +150	
			BDV66C		

THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
R _{thj-c}	Thermal Resistance, Junction to Case	0.625	°C / W

SWITCHING TIMES

Symbol	Ratings	Test Condition(s)	Value			Unit
Symbol	Natings	rest condition(s)	Min	Тур	Max	
t _{on}	turn-on time	I _C = 10 A , V _{CC} = 12 V	-	1	-	
t _{off}	turn-off time	$I_{B1} = -I_{B2} = 40 \text{ mA}$	1	3.5	-	μs

^(*) Pulse Width $\approx 300~\mu s,$ Duty Cycle \angle 1.5 %



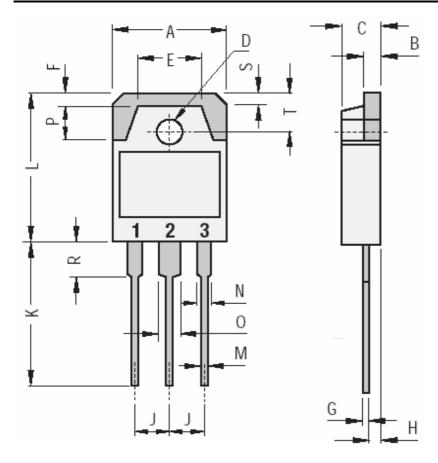
ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

Symbol	Ratings	Test Condition(s)			Min	Тур	Max	Unit
	Collector Cutoff Current	V _{CE} = -40 V, I _B = 0		BDV66	-		-1	mA
		V_{CE} = -50 V, I_{B} = 0		BDV66A				
I _{CEO}		$V_{CE} = -60 \text{ V}, I_{B} = 0$		BDV66B		-		
		$V_{CE} = -70 \text{ V}, I_{B} = 0$		BDV66C				
		V _{BE} = -5 V, I _C = 0		BDV66			_	0
	Emitter Cutoff			BDV66A				
I _{EBO}	Current	$V_{BE}=-5 V,$	I _C = U	BDV66B	Ī -	-	-5	mA
				BDV66C	1			
			V _{CB} = -80 V	BDV66				mA .
		$I_E = 0$	V _{CB} = -100 V	BDV66A	- - -		-1	
	0 " , 0 , "	T _j =25°C	V _{CB} = -120 V	BDV66B		-		
	Collector Cutoff Current		V _{CB} = -140 V	BDV66C				
I _{CBO}		I _E = 0 T _j =150°C	V _{CB} = -40 V	BDV66		-	-5	
			V _{CB} = -50 V	BDV66A				
			V _{CB} = -60 V	BDV66B				
			V _{CB} = -70 V	BDV66C				
	Collector-Emitter Breakdown Voltage (*)	I _C = -100 mA, I _B = 0		BDV66	-60	-	-	V
V				BDV66A	-80	-		
V _{CEO}				BDV66B	-100	-	-	V
				BDV66C	-120	-	-	
	DC Current Gain (*)	V _{CE} = -3 V, I _C = -10 A		BDV66	1000	-	-	-
h _{FE}				BDV66A				
**FE				BDV66B				
				BDV66C				
	Collector-Emitter saturation Voltage (*)	I _C = -10 A, I _B = -40 mA		BDV66	- - - -	_	-2	V
V _{CE(SAT)}				BDV66A				
• CE(SAT)				BDV66B				
				BDV66C				
	Base-Emitter Voltage(*)	V _{CE} = -3 V, I _C = -10 A		BDV66	- - -	-	-2,5	V
V_{BE}				BDV66A				
- 65				BDV66B				
				BDV66C				
	Output Capacitance	V _{CB} = -10 V, I _E = 0 f _{test} = 1 MHz		BDV66	- - -	300	-	pF
Сов				BDV66A				
-05				BDV66B				
				BDV66C				



MECHANICAL DATA CASE TO3PN Non Isolated Plastic Package



DIMENSIONS (mm)					
	Min.	Max.			
Α	15.20	1600			
B C D E	1.90	2.10			
С	4.60	5.00			
D	3.10	3.30			
Е		9.60			
		2.00			
G	0.35	0.55			
H J		1.40			
J	5.35	5.55			
K	20.00)			
L	19.60	20.20			
M	0.95	1.25			
N		2.00			
0		3.00			
Р		4.00			
R		4.00			
S		1.80			
Т	4.80	5.20			
Pin 1	Pin 1 : Base				
Pin 2	:	Collector			

Pin 2 : Collector Pin 3 : Emitter Package Collector

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